

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

Takashi OHSAWA

Serial No.: Continuation of 09/964,851, filed
September 28, 2001

Filed: Herewith

For: SEMICONDUCTOR MEMORY DEVICE

Atty. Docket No.: 002372.00045

Group Art Unit: Unknown

Examiner: Unknown

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

In accordance with Applicants' duty of disclosure, the following information is submitted for consideration by the United States Patent and Trademark Office in connection with the above-captioned application. The information is identified on the attached PTO-1449 form.

This application relies, under 35 U.S.C. § 120, on the earliest filing date of prior U.S. patent application serial no. 09/964,851, filed September 28, 2001. The documents identified on the attached PTO 1449 form were submitted to and/or cited by the Office in a prior application and, therefore, copies are not required to be provided in this application. (See 37 C.F.R. § 1.98(d)).

Applicants do not waive any right to take appropriate action to establish patentability over the listed documents should they be applied as references against the claims of the present application.

It is respectfully requested that the Examiner fully consider each of the documents, initial the enclosed Form PTO-1449 in the appropriate place to indicate that the document has been

considered, and return a copy of the initialed form to the undersigned in accordance with MPEP Section 609.

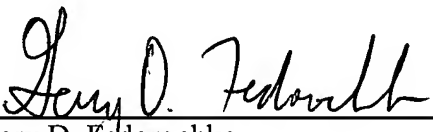
Applicants believe that no fee is necessary pursuant to 37 C.F.R. § 1.97(b). However, if a fee is due, the Office is authorized to charge Deposit Account No. 19-0733.

Respectfully submitted,

BANNER & WITCOFF, LTD.

Dated: July 14, 2003

By:



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GDF:lab

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PTO/SB/08A (08-00)

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Substitute for form 1449A/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet

1

of

1

Complete if Known

Application Number

TBA

Filing Date

Herewith

First Named Inventor

Takashi OHSAWA

Group Art Unit

Unknown

Examiner Name

Unknown

Attorney Docket Number

002372.00045

U.S. PATENT DOCUMENTS

Examiner Initials *	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
		5,506,436		Hayashi et al.	04-1996	
		5,567,959		Mineji	10-1996	
		2002-0051378	A1	Ohsawa	05-02-02	
		2002-0034855	A1	Horiguchi	03-21-02	

FOREIGN PATENT DOCUMENTS

Examiner Initials *	Cite No. ¹	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ₆
		Office ³	Number ⁴	Kind Code ⁵ (if known)				
		JP	03-171768		Sakui	07-25-91		Abst
		JP	07-30001	A	Oda et al.	01-1995		

OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials *	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
		G. VINCENT, et al., "Electric field effect on the thermal emission of traps in semiconductor junctions", 1979 American Institute of Physics, pp. 5484-5487	
		J. LEISS, et al., "dRAM Design Using the Taper-Isolated Dynamic RAM Cell", IEEE Transactions on Electron Devices, Vol. ED-29, No. 4, April 1982, pp. 707-714	
		M. TACK, et al., "The Multistable Charge-Controlled Memory Effect in SOI MOS Transistors at Low Temperatures", IEEE Transactions on Electron Devices, Vol. 37, No. 5, May 1990, pp. 1373-1382	
		H. WANN, et al., "A Capacitorless DRAM Cell on SOI Substrate", 1993 IEEE, pp. 635-638	
		P. CHATTERJEE, et al., "Memory Technology", Digest of Technical Papers, February 1979, pp. 22-23	

Examiner
Signature

Date
Considered

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.